

What is claimed is:

1. A method of contacting terminals, the method comprising:

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providing a substrate having a substrate surface, the substrate comprising a first terminal having a first terminal surface, and a second terminal having a second terminal surface, wherein a distance between the first terminal surface and the substrate surface is smaller than a distance between the second terminal surface and the substrate surface;

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forming a first insulating layer on the substrate surface and on the first and second terminal surfaces;

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forming a contact via in the first insulating layer for exposing the first terminal surface;

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filling the contact via with a conductive material;

forming a second insulating layer on the first insulating layer and on the contact via filled with the conductive material;

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forming an etching mask on the second insulating layer, the etching mask specifying an area for a first contact terminal and an area for a second contact terminal;

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etching a first recess through the second insulating layer for exposing the conductive material filling the contact via, and etching a second recess through the second and first insulating layers for exposing the second terminal surface using the etching mask;

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introducing a conductive material into the first recess and into the second recess for producing the first and second contact terminals.

2. The method as claimed in claim 1, wherein the first terminal is a base terminal or a collector terminal, and the second terminal is an emitter terminal, arranged on a
5 stack, of a bipolar transistor.

3. The method as claimed in claim 1, wherein the first terminal is a source or a drain terminal, and the second terminal is a gate terminal of a field-effect transistor.

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4. The method as claimed in claim 1, wherein one or several first terminals are provided on the substrate, which are a base terminal or a collector terminal of a bipolar transistor, or a gate terminal, a source terminal or a drain terminal of a field-effect transistor,
15 respectively.

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5. The method as claimed in claim 1, wherein the conductive material filling the first recess, and/or the conductive material filling the second recess consist of metal.

6. The method as claimed in claim 1, wherein the conductive material filling the contact via is tungsten.

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7. The method as claimed in claim 1, wherein the conductive material introduced into the first and second recesses is copper.

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8. The method as claimed in claim 1, wherein the first contact terminal and the second contact terminal form a wiring plane.

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9. The method as claimed in claim 1, wherein the step of forming the contact via includes etching the contact via.

10. The method as claimed in claim 1, wherein the first recess and the second recess are etched in one pass.

11. The method as claimed in claim 1, wherein the conductive material is introduced into the first and second recesses, so that the first and second contact terminals
5 are produced in one pass.

12. An arrangement for contacting terminals of a substrate comprising a substrate surface, a first terminal having a first terminal surface, and a second terminal having a second terminal surface, the first terminal surface being located at a shorter distance from the substrate surface than the second terminal surface, the arrangement comprising:
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15 a first insulating layer on the substrate surface, having an insulation-layer surface being located at a longer distance from the substrate surface than the second terminal surface;

20 a second insulating layer arranged on the first insulating layer;

wherein the first insulating layer has a contact via which extends from the insulation-layer surface to the first
25 terminal surface and is filled with a first conductive material, and wherein the second insulating layer has a recess penetrating the former, extending up to the first conductive material, and being filled with a second conductive material; and
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wherein a recess extends to the second terminal surface through the first and second insulating layers, and is filled with a third conductive material.

35 13. The arrangement as claimed in claim 12, wherein the first terminal is a base terminal or a collector terminal, and the second terminal is an emitter terminal, arranged on a stack, of a bipolar transistor.

14. The arrangement as claimed in claim 12, wherein the first terminal is a source or a drain terminal, and the second terminal is a gate terminal of a field-effect
5 transistor.

15. The arrangement as claimed in claim 12, wherein one or several first terminals are formed on the substrate, which are a base terminal or a collector terminal of a bipolar
10 transistor, or a gate terminal, a source terminal or a drain terminal of a field-effect transistor, respectively.

16. The arrangement as claimed in claim 12, wherein the first conductive material and/or the second conductive
15 material and/or the third conductive material consist of metal.

17. The arrangement as claimed in claim 12, wherein the first conductive material is tungsten.

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18. The arrangement as claimed in claim 12, wherein the second and/or third conductive materials is/are copper.

19. The arrangement as claimed in claim 12, wherein the
25 second conductive material is conductively connected to the first conductive material and forms a first contact terminal, and wherein the third conductive material is conductively connected to the second terminal and forms a second contact terminal.

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20. The arrangement as claimed in claim 12, wherein the first and second contact terminals form a wiring plane.